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## Deposition of Ferroelectric Thin Films by MOCVD

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Ferroelectric thin films are materials of great interest for various applications such as nonvolatile memory devices, high dielectric constant capacitors in ULSI DRAMs and electro-optic devices. Recently, among them PZT and BST thin films have especially become very attractive due to their high dielectric constants. MOCVD is one of the most suitable methods for the deposition of multi-component oxide thin films such as PZT and BST since it offers a very convenient mean of composition control. Moreover, recent developments of metal-organic source materials such as  $\beta$ -diketonate compounds allow the deposition of ferroelectric thin films at low temperatures. In this presentation, I will talk about the research trend of ferroelectric thin films, deposition of PZT and BST thin films by MOCVD and problems to be solved to apply such ferroelectric thin films for the electronic devices.